

ABSTRACT

A semiconductor wafer structure which includes at least one bipolar transistor defined in the semiconductor wafer structure as well as at least one CMOS transistor device also defined in the semiconductor wafer structure. The CMOS transistor device is comprised of a thin film of semiconductor on an insulating layer with each transistor of the CMOS transistor device being defined in the thin film. The bipolar transistor has a plurality of semiconductor layers of predetermined conductivities, without any of the semiconductor layers of the bipolar transistor extending into the area occupied by the CMOS transistor device. A method of fabricating the structure is also disclosed.